UN1596

Preliminary

NPN SILICON TRANSISTOR

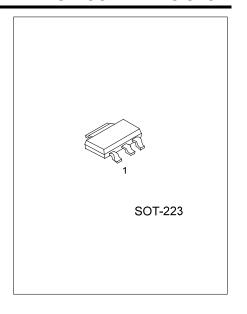
NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

■ DESCRIPTION

The UTC **UN1596** are series of NPN silicon planar transistor, which has gain of 500 at I_C =100mA.It can be used in such applications: battery powered circuit and darlington replacement.

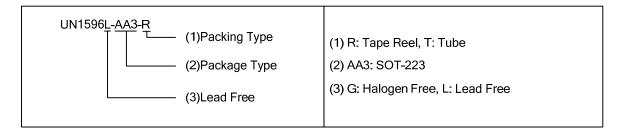
■ FEATURES

- * Gain :500 @ I_C=100mA
- * Low saturation voltage



■ ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UN1596L-AA3-R	UN1596G-AA3-R	SOT-223	В	С	Е	Tape Reel	



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ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	180	V
Collector-Emitter Voltage		$V_{\sf CEO}$	180	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		Ic	0.5	Α
Peak Pulse Current		I _{CM}	1	Α
Collector Power dissipation	T _A =25°C	Pc	2	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	−55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA	180			٧		
Collector-Emitter Breakdown Voltage	BV _{CEO} I _C =10mA		180			V		
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =100μA	5			V		
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	I _C =200mA, V _{CE} =5V			0.9	V		
Collector Cutoff Current	I_{CBO}	V _{CB} =140V			100	nA		
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V			100	nA		
ON CHARACTERISTICS								
	V _{CE(SAT)}	I _C =50mA, I _B =0.5mA		0.2		V		
Collector-Emitter Saturation Voltage		I _C =100mA, I _B =2mA		0.2				
		I _C =250mA, I _B =5mA		0.25				
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I _C =20mA, I _B =5mA			0.9	V		
DO C Transfer Bullin	h _{FE}	I _C =100mA, V _{CE} =5V	500					
DC Current Transfer Ratio		I _C =200mA, V _{CE} =5V	150					
SMALL-SIGNAL CHARACTERISTIC	S							
Transition Frequency	f _T	I _C =50mA, V _{CE} =5V, f=50MHz	70			MHz		
Input Capacitance	Cı	V _{EB} =0.5V, f=1MHz			200	pF		
Output Capacitance	Co	V _{CB} =10V, f=1MHz			6	pF		
O Malina Timas	t _{ON}	I _C =100mA, I _{B1} =10mA		80				
Switching Times	t _{OFF}	I _{B2} =10mA, V _{CC} =50V		4400		ns		

Note: Pulse width=300 μ s. Duty cycle \leq 2%

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